

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

(PTO-1449)

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67161-138

SERIAL NO.
Divisional of Appl. No.
10/170,580

APPLICANT
Tsukasa OOISHI

FILING DATE
February 13, 2004

GROUP

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number & Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
18		JP 10-106255 A	04/24/1998	TOSHIBA CORP.			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>LP</i>		"A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in Each Cell", Scheuerlein et al., ISSCC Digest of Technical Papers, TA7.2, Feb. 2000, pp. 94-95, 128-129, 409-410.
<i>LP</i>		"Nonvolatile RAM based on Magnetic Tunnel Junction Elements", Durlam et al., ISSCC Digest of Technical Papers, TA7.3, Feb. 2000, pp. 96-97, 130-131, 410-411.
		<i>LP</i>

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~~DATE CONSIDERED~~

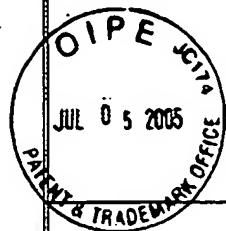
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INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.
067161-0138SERIAL NO.
10/777,069APPLICANT
Tsukasa OOISHIFILING DATE
February 13, 2004GROUP
2824 2827

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
LP	US	6,608,776 B2	08/19/2003	Hidaka	Counterpart of DE 101 23 332
	US	2004/0047196 A1	03/11/2004	Hidaka	Counterpart of DE 101 23 332
	US	6,778,430 B2	08/17/2004	Hidaka	Counterpart of DE 101 33 646 A1
	US	5,894,447	04/13/1999	Takashima	Counterpart of JP 10-106255
	US	5,732,016	03/24/1998	Chen et al.	Counterpart of DE 197 26 077 A1
	US	5,920,500	07/06/1999	Tehrani et al.	Counterpart of DE 197 26 852 A1
	US	5,946,227	08/31/1999	Naji	
	US	5,448,515	09/05/1995	Fukami et al.	
↓	US	5,734,606	03/31/1998	Tehrani et al.	

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EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code-Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No
LP		DE 101 23 332	11/28/2002	MITSUBISHI DENKI K.K.	Counterpart of USP 6,608,776 B2 & USP 2004/0047196 A1	
		DE 101 33 646 A1	04/18/2002	MITSUBISHI DENKI K.K.	Counterpart of USP 6,778,430 B2	X
		JP 10-106255	04/24/1998	TOSHIBA CORP	Counterpart of USP 5,894,447	JAPAN (w/English Abstract)
		DE 197 26 077 A1	01/08/1998	MOTOROLA, INC	Counterpart of USP 5,732,016	X
		DE 197 26 852 A1	02/26/1998	MOTOROLA, INC	Counterpart of USP 5,920,500	X
↓		EP 0 507 451 A2	10/07/1992	MITSUBISHI DENKI KABUSHIKI		X

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
LP		Durham, M. et al., "Nonvolatile RAM based on magnetic tunnel junction elements" IEEE International Solid-State Circuits Conference, 7 to 9 February 2000, pp. 130-131.
LP		Scheuerlein, R. et al., "A 10ns read and write nonvolatile memory array using a magnetic tunnel junction and FET switch in each cell" IEEE International Solid-State Circuits Conference, 7 to 9 February 2000, pp. 128-129.

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